

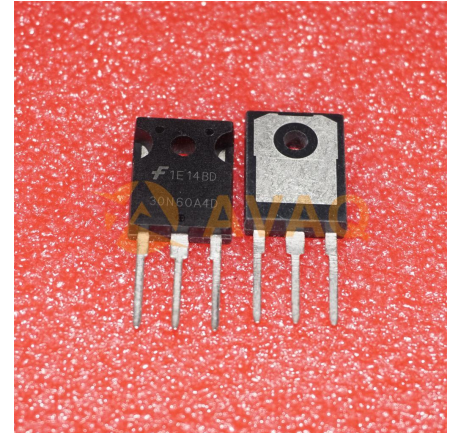
600V, SMPS IGBT

Manufacturer: [ON Semiconductor, LLC](#)

Package/Case: TO-247

Product Type: Thyristors

Lifecycle: LTB



Images are for reference only

[Inquiry](#)

General Description

HGTG30N60A4D is a power transistor module produced by the semiconductor manufacturer Infineon. It is a type of insulated gate bipolar transistor (IGBT) that is designed to handle high power and high voltage applications. Here are some of its features:

Key Features

Collector-emitter voltage (V_{ce}): 600V

Collector current (I_c): 75A

Maximum power dissipation (P_d): 450W

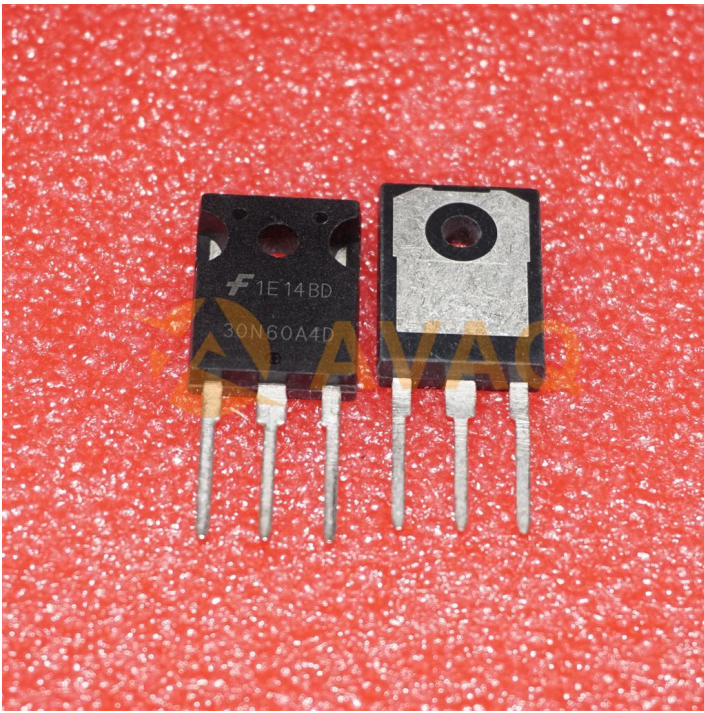
Fast switching speed for efficient power conversion

Low saturation voltage for reduced power loss

Thermal conductivity for efficient heat dissipation

Application

AC-DC Merchant Power Supply - Servers & Workstations



Recommended For You

HGTG20N60B3D

ON Semiconductor, LLC

TO-247

HGTG11N120CND

ON Semiconductor, LLC

TO-247

HGTG20N60B3

ON Semiconductor, LLC

TO-247

HGTP3N60A4

ON Semiconductor, LLC

TO-220

HGTG11N120CN

ON Semiconductor, LLC

TO-247

HGTG12N60A4D

ON Semiconductor, LLC

TO-247

HGTP7N60C3D

ON Semiconductor, LLC

TO-220

HGTG10N120BND

ON Semiconductor, LLC

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HGTP10N120BN

ON Semiconductor, LLC

TO-220

HGTG27N120BN

ON Semiconductor, LLC

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HGTG30N60C3D

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HGTG30N60B3

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HGTP7N60B3D

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HGTG40N60B3

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HGTG40N60A4

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